



PH2625L

N-channel TrenchMOS™ logic level FET

Rev. 02 — 24 February 2005

Preliminary data sheet

1. Product profile

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS™ technology.

1.2 Features

- Optimized for use in DC-to-DC converters
- Low threshold voltage
- Very low switching and conduction losses
- Low thermal resistance.

1.3 Applications

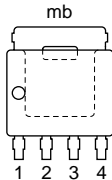
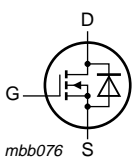
- DC-to-DC converters
- Voltage regulators
- Switched-mode power supplies
- Notebook computers.

1.4 Quick reference data

- $V_{DS} \leq 25$ V
- $Q_{gd} = 7.3$ nC (typ)
- $R_{DSon} \leq 2.8$ m Ω ($V_{GS} = 10$ V)
- $I_D \leq 100$ A
- $Q_{g(tot)} = 32$ nC (typ)
- $R_{DSon} \leq 4.1$ m Ω ($V_{GS} = 4.5$ V).

2. Pinning information

Table 1: Pinning

Pin	Description	Simplified outline	Symbol
1, 2, 3	source		
4	gate		
mb	mounting base; connected to drain		

SOT669 (LFPAK)

PHILIPS

3. Ordering information

Table 2: Ordering information

Type number	Package		Version
	Name	Description	
PH2625L	LFAK	plastic single-ended surface mounted package; 4 leads	SOT669

4. Limiting values

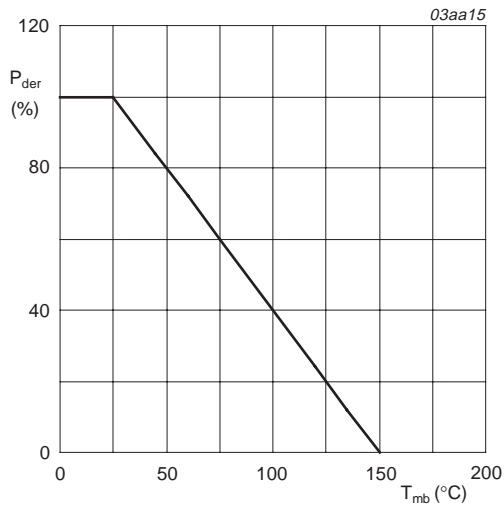
Table 3: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}$	-	25	V
V_{DGR}	drain-gate voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	25	V
V_{GS}	gate-source voltage		-	± 20	V
I_D	drain current (DC)	$T_{mb} = 25\text{ °C}$; $V_{GS} = 10\text{ V}$; Figure 2 and 3	-	100	A
		$T_{mb} = 100\text{ °C}$; $V_{GS} = 10\text{ V}$; Figure 2	-	63	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Figure 3	-	300	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Figure 1	-	62.5	W
T_{stg}	storage temperature		-55	+150	°C
T_j	junction temperature		-55	+150	°C
Source-drain diode					
I_S	source (diode forward) current (DC)	$T_{mb} = 25\text{ °C}$	-	52	A
I_{SM}	peak source (diode forward) current	$T_{mb} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$	-	156	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	unclamped inductive load; $I_D = 71\text{ A}$; $t_p = 0.1\text{ ms}$; $V_{DD} \leq 25\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$; starting at $T_j = 25\text{ °C}$	-	250	mJ
$E_{DS(AL)R}$	repetitive drain-source avalanche energy	unclamped inductive load; $I_D = 7.1\text{ A}$; $t_p = 0.01\text{ ms}$; $V_{DD} \leq 25\text{ V}$; $R_{GS} = 50\text{ }\Omega$; $V_{GS} = 10\text{ V}$	[1] [2]	2.5	mJ

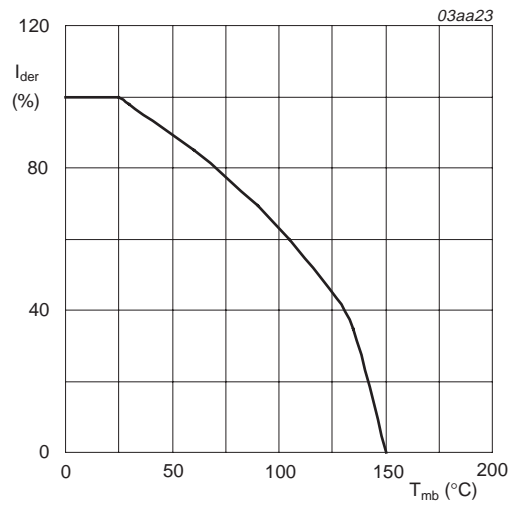
[1] Duty cycle is limited by the maximum junction temperature.

[2] Repetitive avalanche failure is not determined simply by thermal effects. Repetitive avalanche transients should only be applied for short bursts, not every switching cycle.



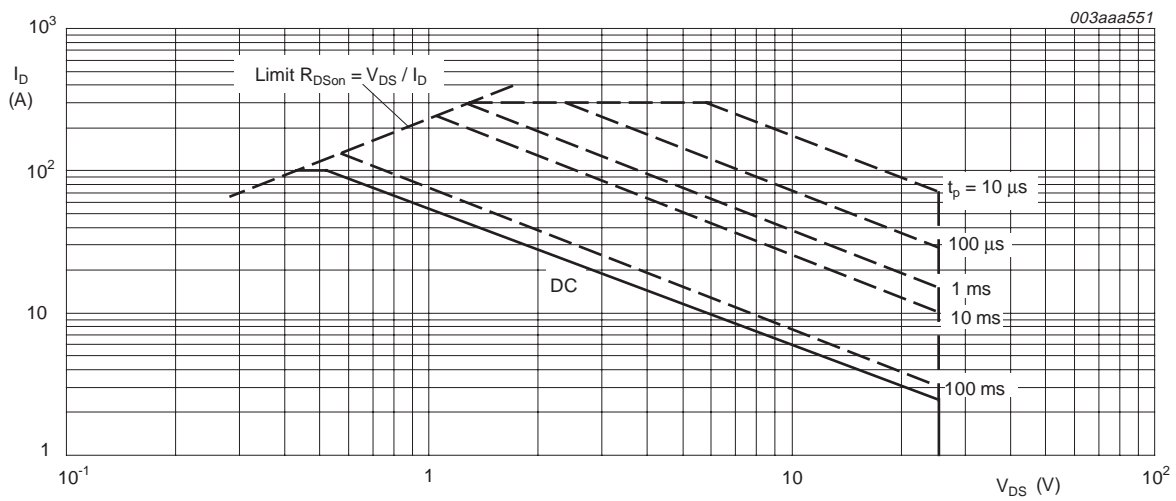
$$P_{der} = \frac{P_{tot}}{P_{tot(25\text{ }^\circ\text{C})}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature



$$I_{der} = \frac{I_D}{I_{D(25\text{ }^\circ\text{C})}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of mounting base temperature



$T_{mb} = 25\text{ }^\circ\text{C}$; I_{DM} is single pulse; $V_{GS} = 10\text{ V}$

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Figure 4	-	-	2	K/W

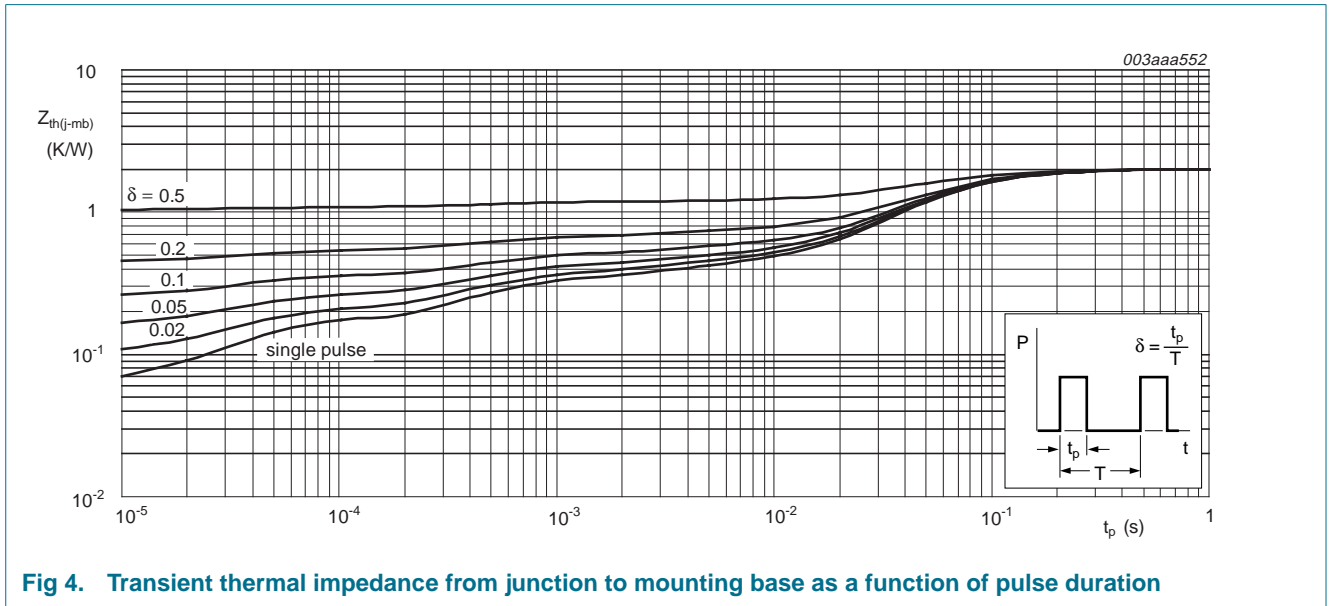
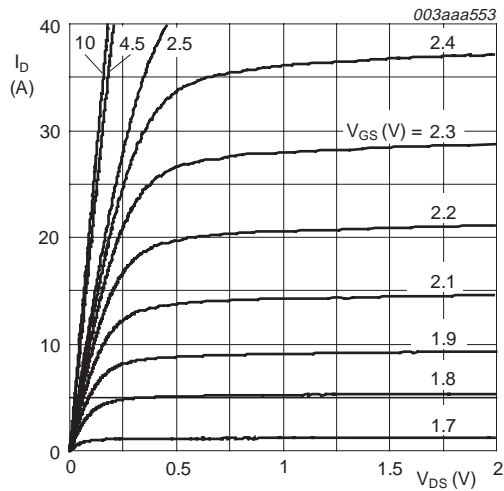


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

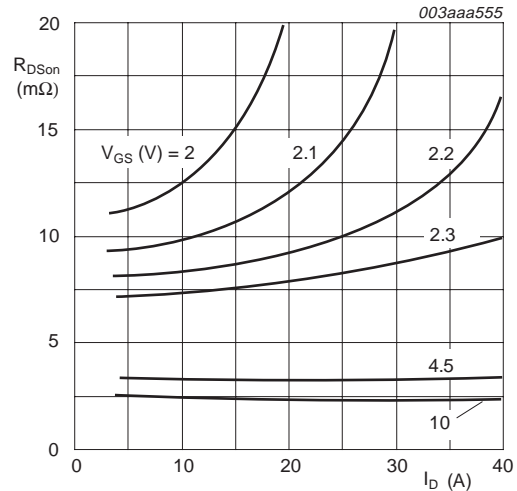
Table 5: Characteristics
 $T_j = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$; $V_{GS} = 0\ \text{V}$	25	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\ \text{mA}$; $V_{DS} = V_{GS}$; Figure 9 and 10				
		$T_j = 25\text{ °C}$	1	1.5	2	V
		$T_j = 150\text{ °C}$	0.5	-	-	V
		$T_j = -55\text{ °C}$	-	-	2.2	V
I_{DSS}	drain-source leakage current	$V_{DS} = 25\ \text{V}$; $V_{GS} = 0\ \text{V}$				
		$T_j = 25\text{ °C}$	-	0.06	1	μA
		$T_j = 150\text{ °C}$	-	-	500	μA
R_G	gate resistance	$f = 1\ \text{MHz}$	-	1.5	-	Ω
I_{GSS}	gate-source leakage current	$V_{GS} = \pm 16\ \text{V}$; $V_{DS} = 0\ \text{V}$	-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\ \text{V}$; $I_D = 25\ \text{A}$; Figure 6 and 8				
		$T_j = 25\text{ °C}$	-	2	2.8	m Ω
		$T_j = 150\text{ °C}$	-	3.2	4.3	m Ω
		$V_{GS} = 4.5\ \text{V}$; $I_D = 25\ \text{A}$; Figure 6 and 8				
		$T_j = 25\text{ °C}$	-	3	4.1	m Ω
		$T_j = 150\text{ °C}$	-	4.8	6.6	m Ω
Dynamic characteristics						
$Q_{g(tot)}$	total gate charge	$I_D = 25\ \text{A}$; $V_{DS} = 12\ \text{V}$; $V_{GS} = 4.5\ \text{V}$; Figure 11 and 12	-	32	-	nC
Q_{gs}	gate-source charge		-	9.6	-	nC
Q_{gs1}	pre- $V_{GS(th)}$ gate-source charge		-	6	-	nC
Q_{gs2}	post- $V_{GS(th)}$ gate-source charge		-	3.6	-	nC
Q_{gd}	gate-drain (Miller) charge		-	7.3	-	nC
V_{plat}	plateau voltage		-	2.2	-	V
$Q_{g(tot)}$	total gate charge	$I_D = 0\ \text{A}$; $V_{DS} = 0\ \text{V}$; $V_{GS} = 4.5\ \text{V}$	-	26	-	nC
C_{iss}	input capacitance	$V_{GS} = 0\ \text{V}$; $V_{DS} = 12\ \text{V}$; $f = 1\ \text{MHz}$; Figure 13 and 14	-	4308	-	pF
C_{oss}	output capacitance		-	1137	-	pF
C_{riss}	reverse transfer capacitance		-	439	-	pF
C_{iss}	input capacitance	$V_{GS} = 0\ \text{V}$; $V_{DS} = 0\ \text{V}$; $f = 1\ \text{MHz}$	-	4830	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 12\ \text{V}$; $R_L = 0.48\ \Omega$; $V_{GS} = 4.5\ \text{V}$; $R_G = 4.7\ \Omega$	-	41	-	ns
t_r	rise time		-	52	-	ns
$t_{d(off)}$	turn-off delay time		-	67	-	ns
t_f	fall time		-	30	-	ns
Source-drain diode						
V_{SD}	source-drain (diode forward) voltage	$I_S = 25\ \text{A}$; $V_{GS} = 0\ \text{V}$; Figure 15	-	0.85	1.2	V
t_{rr}	reverse recovery time	$I_S = 20\ \text{A}$; $di_S/dt = -100\ \text{A}/\mu\text{s}$; $V_{GS} = 0\ \text{V}$; $V_R = 25\ \text{V}$	-	47	-	ns
Q_r	recovered charge		-	22	-	nC



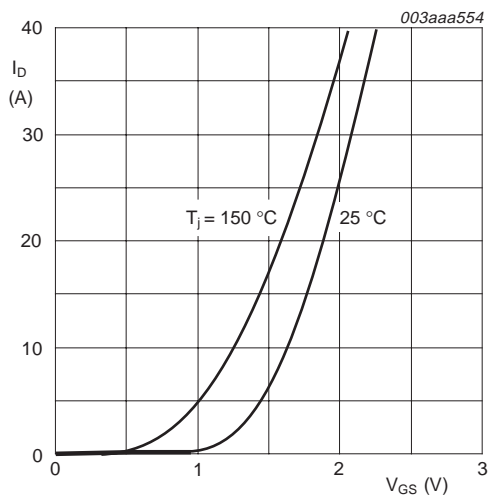
$T_j = 25\text{ }^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



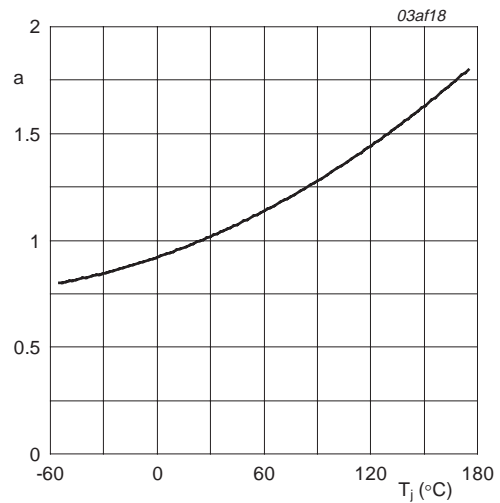
$T_j = 25\text{ }^\circ\text{C}$

Fig 6. Drain-source on-state resistance as a function of drain current; typical values



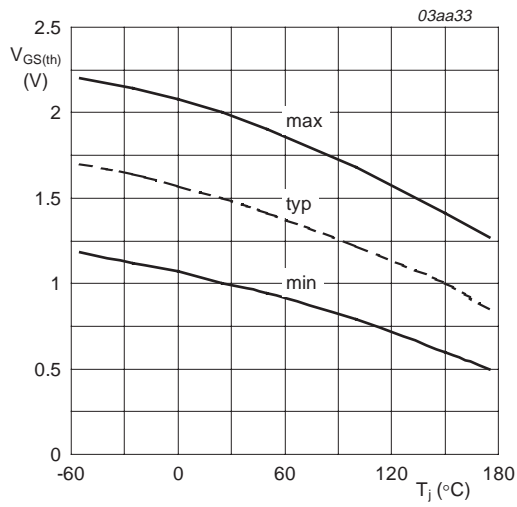
$T_j = 25\text{ }^\circ\text{C}$ and $150\text{ }^\circ\text{C}$; $V_{DS} > I_D \times R_{DS(on)}$

Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



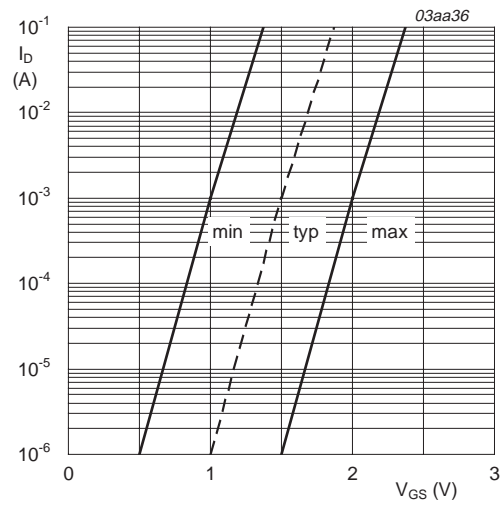
$$a = \frac{R_{DS(on)}}{R_{DS(on)(25\text{ }^\circ\text{C})}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature



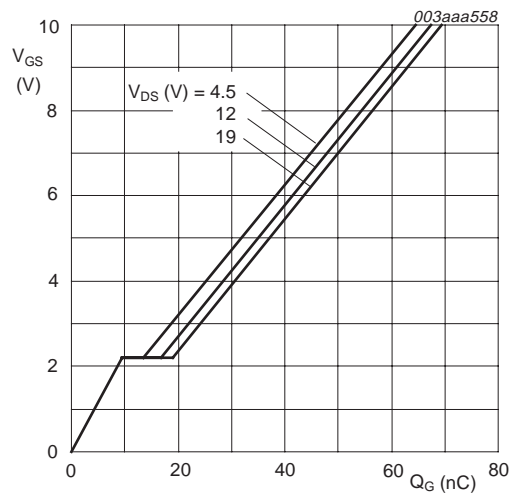
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature



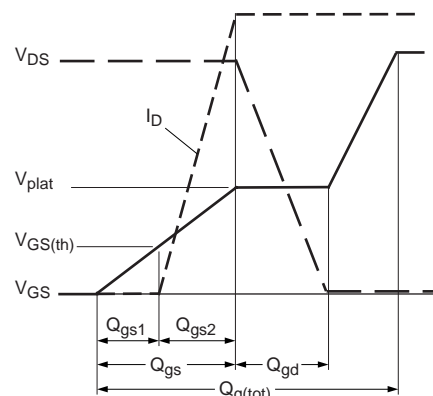
$T_j = 25 \text{ °C}; V_{DS} = 5 \text{ V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



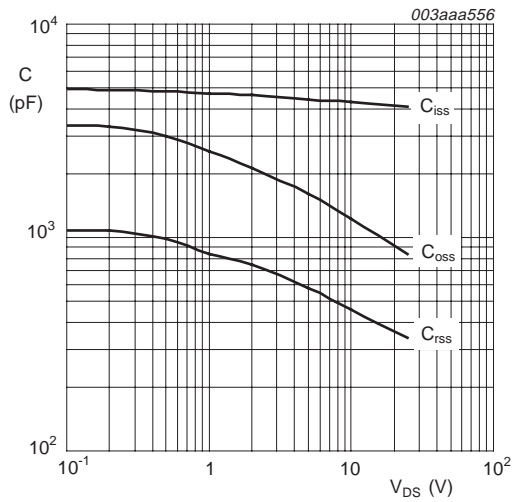
$I_D = 25 \text{ A}; V_{DS} = 4.5 \text{ V}, 12 \text{ V and } 19 \text{ V}$

Fig 11. Gate-source voltage as a function of gate charge; typical values



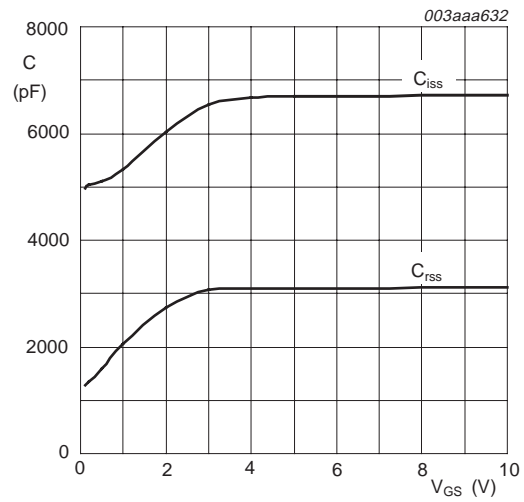
003aaa508

Fig 12. Gate charge waveform definitions



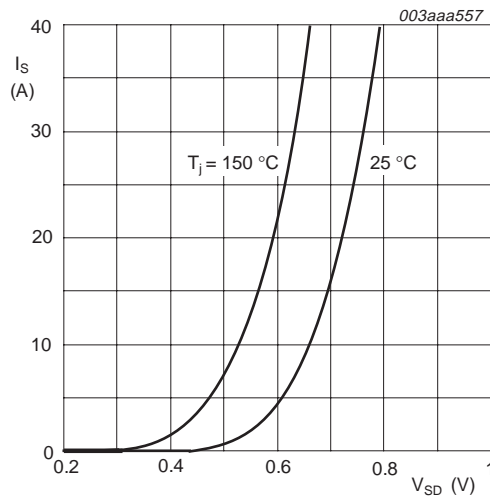
V_{GS} = 0 V; f = 1 MHz

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



V_{DS} = 0 V; f = 1 MHz

Fig 14. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



T_j = 25 °C and 150 °C; V_{GS} = 0 V

Fig 15. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended surface mounted package (LPAK); 4 leads

SOT669

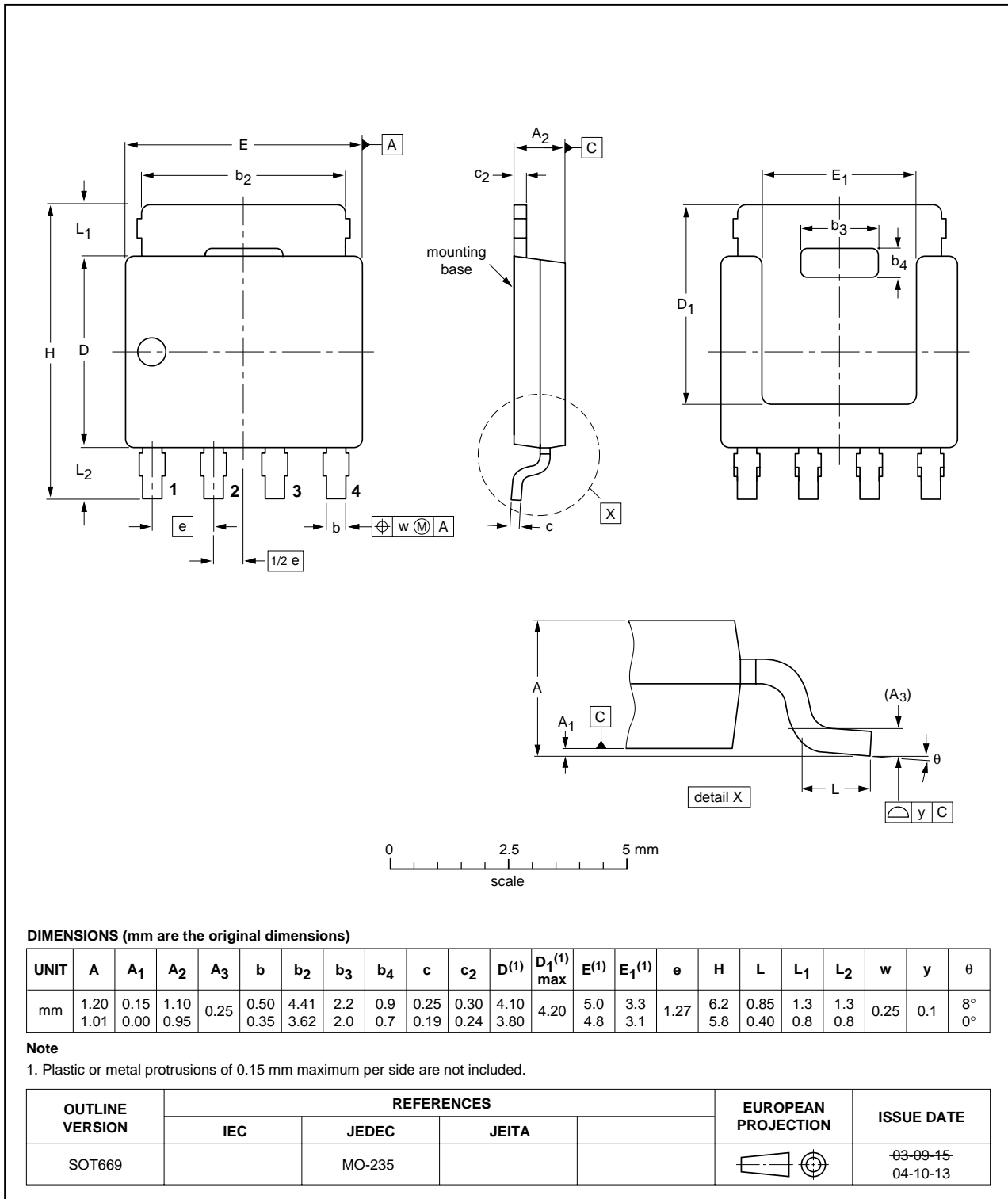
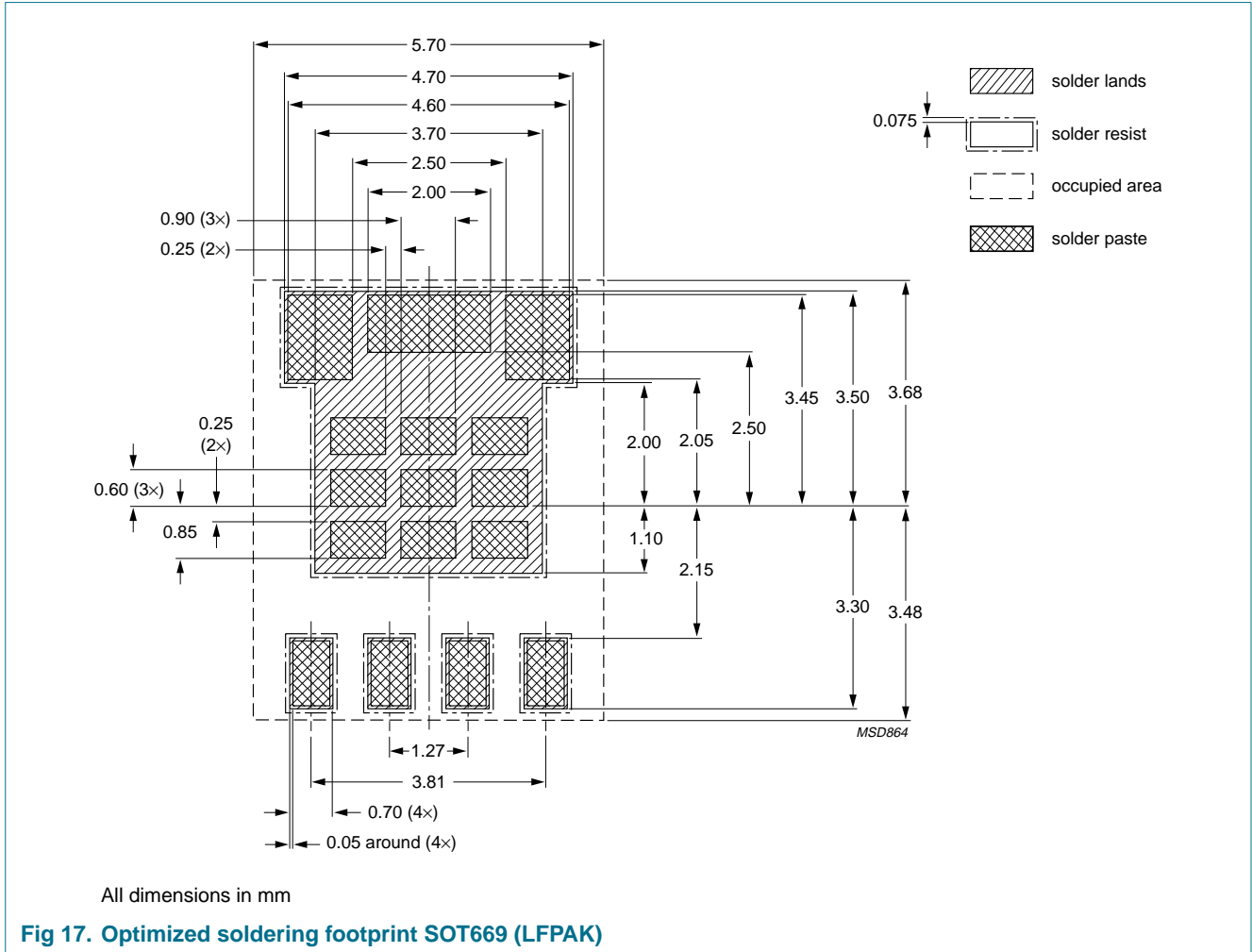


Fig 16. Package outline SOT669 (LPAK)

8. Soldering



9. Revision history

Table 6: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PH2625L_2	20050224	Preliminary data sheet	-	9397 750 14324	PH2625L-01
Modifications:	<ul style="list-style-type: none">The format of this data sheet has been redesigned to comply with the new presentation and information standard of Philips Semiconductors.R_{DSon} data revised in Section 1.4 “Quick reference data” and Section 6 “Characteristics”				
PH2625L-01	20040428	Preliminary data sheet	-	9397 750 12306	-

10. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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